Lonten N-channel 600V, 20A, 0.17Ω LonFET™ Power MOSFET

Description

LonFET™ Power MOSFET is fabricated using advanced super junction technology. The resulting device has extremely low on resistance, making it especially suitable for applications which require superior power density and outstanding efficiency.

Features

- Ultra low $R_{DS(on)}$
- Ultra low gate charge (typ. Q_g = 39nC)
- 100% UIS tested
- RoHS compliant

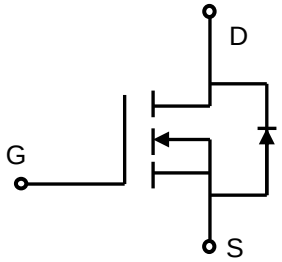
Applications

- Power faction correction (PFC).
- Switched mode power supplies (SMPS).
- Uninterruptible power supply (UPS).

Product Summary

V_{DS} @ $T_{j,max}$	650V
$R_{DS(on),max}$	0.17Ω
I_{DM}	60A
$Q_{g,typ}$	39nC

TO-247 **TO-220MF**



N-Channel MOSFET

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	600	V
Continuous drain current (T_C = 25°C)	I_D	20	A
(T_C = 100°C)		13	A
Pulsed drain current [1]	I_{DM}	60	A
Gate-Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse [2]	E_{AS}	600	mJ
Avalanche energy, repetitive [3]	E_{AR}	0.4	mJ
Avalanche current, repetitive [3]	I_{AR}	20	A
Power Dissipation TO-247 (T_C = 25°C)	P_D	205	W
- Derate above 25°C		1.64	W/°C
Power Dissipation TO-220MF (T_C = 25°C)		34	W
- Derate above 25°C		0.28	W/°C
Mounting torque To-220MF (M2.5 screws)		50	Ncm
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Continuous diode forward current	I_S	20	A
Diode pulse current	$I_{S,pulse}$	60	A

Thermal Characteristics TO-247

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.61	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	60	°C/W
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	°C

Thermal Characteristics TO-220MF

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.6	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	80	°C/W
Soldering temperature, wavesoldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	°C

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Real
LSB60R170GT	TO-247	LSB60R170GT	30	
LSD60R170GT	TO-220MF	LSD60R170GT	50	

Electrical Characteristics

T_c = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=0.25 mA	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.25mA	2.5	3.5	4.5	V
Drain cut-off current	I_{DSS}	V_{DS}=600 V, V_{GS}=0 V, T_j = 25°C T_j = 125°C	 - -	 - 10	 1 -	μA
Gate leakage current, Forward	I_{GSSF}	V_{GS}=30 V, V_{DS}=0 V	-	-	100	nA
Gate leakage current, Reverse	I_{GSSR}	V_{GS}=-30 V, V_{DS}=0 V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=10 A T_j = 25°C T_j = 150°C	- - -	 0.14 0.37	 0.17 -	Ω
Gate resistance	R_G	f=1 MHz, open drain	-	4.5	-	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	-	2637	-	pF
Output capacitance	C_{oss}		-	1250	-	
Reverse transfer capacitance	C_{rss}		-	17	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 380V, I_D = 10A R_G = 4.7Ω, V_{GS}=10V	-	23	-	ns
Rise time	t_r		-	33	-	
Turn-off delay time	$t_{d(off)}$		-	113	-	
Fall time	t_f		-	11	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DD}=480 V, I_D=10A,	-	10.3	-	

Gate to drain charge	Q_{gd}	V_{GS}=0 to 10 V	-	13.7	-	nC
Gate charge total	Q_g		-	39	-	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=10A	-	-	1.2	V
Reverse recovery time	t_{rr}	V_R=50 V, I_F=20A,	-	345	-	ns
Reverse recovery charge	Q_{rr}	dI_F/dt=100 A/μs	-	3.8	-	μC
Peak reverse recovery current	I_{rrm}		-	22	-	A

Notes:

1. Limited by maximum junction temperature, maximum duty cycle is 0.75.

2. I_{AS} = 5A, V_{DD} =60V, Starting T_j= 25°C.

3. Repetitive Rating: Pulse width limited by maximum junction temperature.

Electrical Characteristics Diagrams

Figure 1. On-Region Characteristics

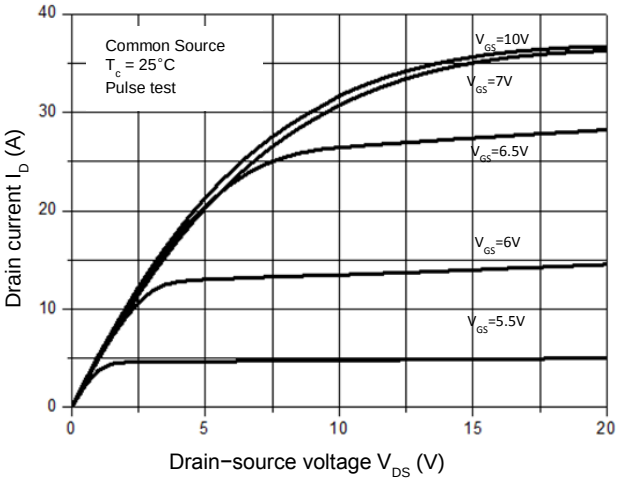


Figure 2. Transfer Characteristics

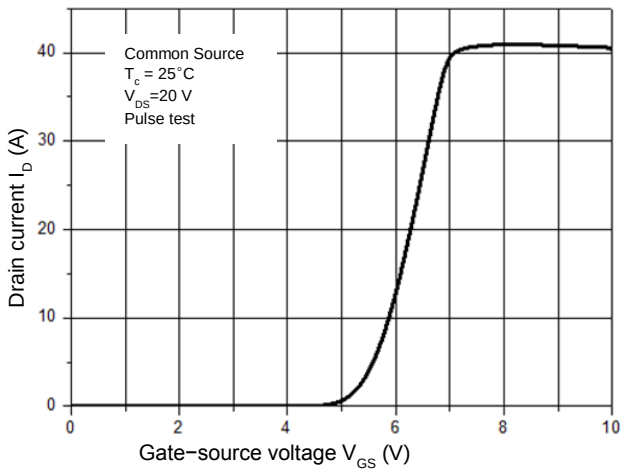


Figure 3. On-Resistance Variation vs. Drain Current

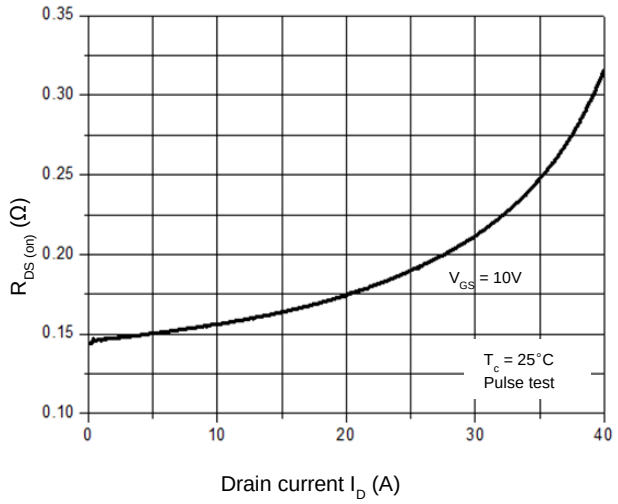


Figure 4. Threshold Voltage vs. Temperature

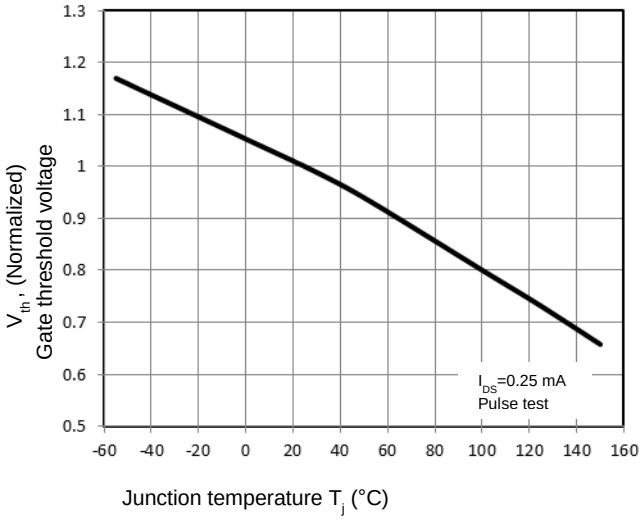


Figure 5. Breakdown Voltage vs. Temperature

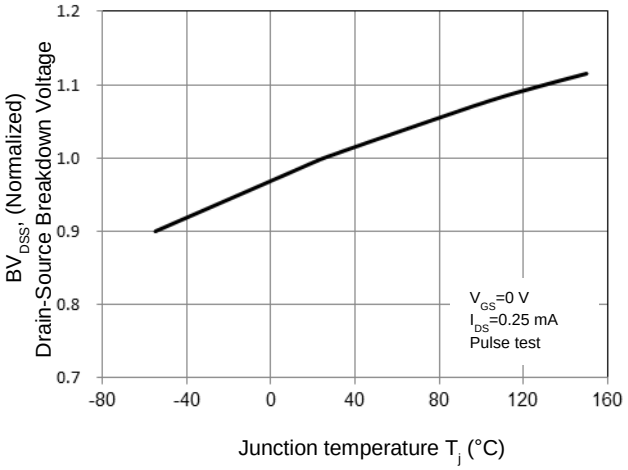


Figure 6. On-Resistance vs. Temperature

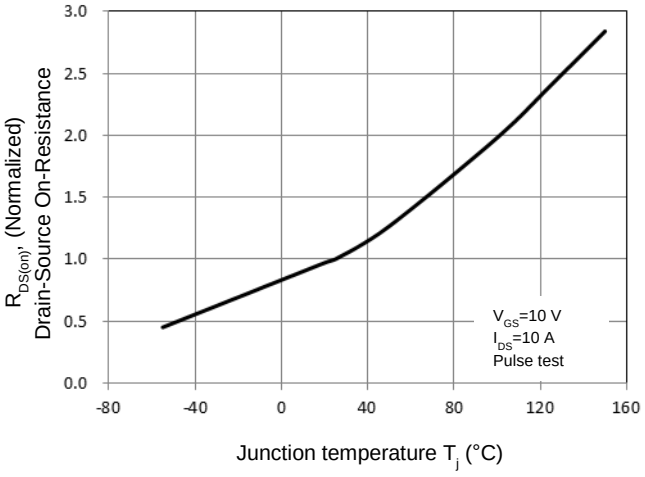


Figure 7. Capacitance Characteristics

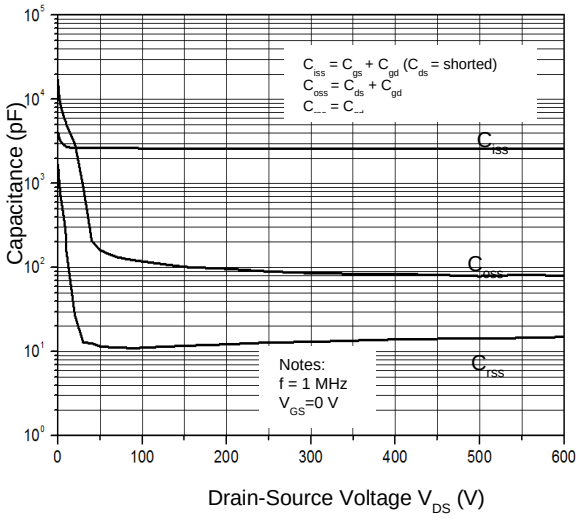


Figure 8. Gate Charge Characterist

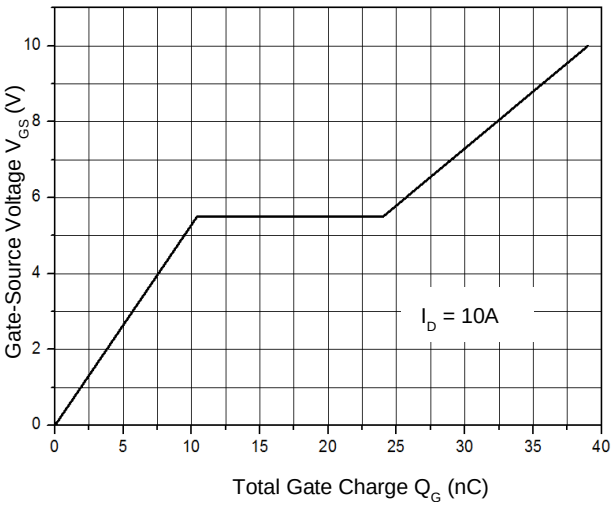


Figure 9.1 Maximum Safe Operating Area
TO-220MF

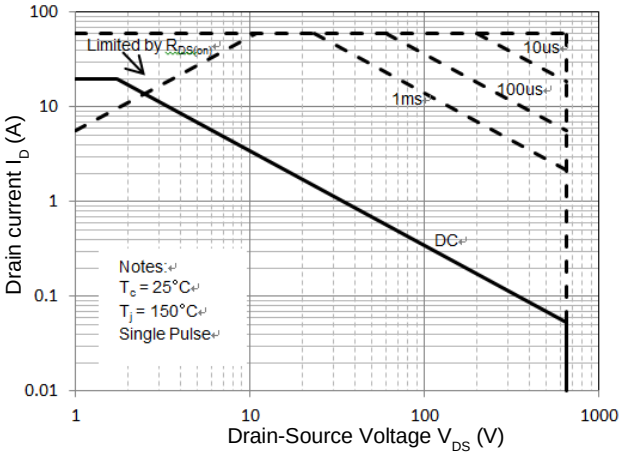


Figure 9.2 Maximum Safe Operating Area
TO-247

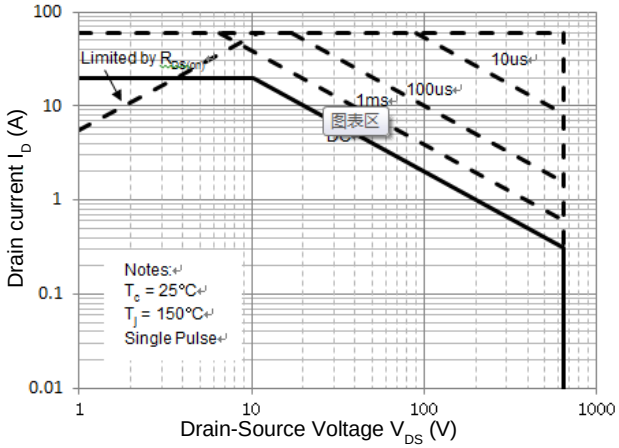


Figure 10.1 Power Dissipation vs. Temperature
TO-220MF

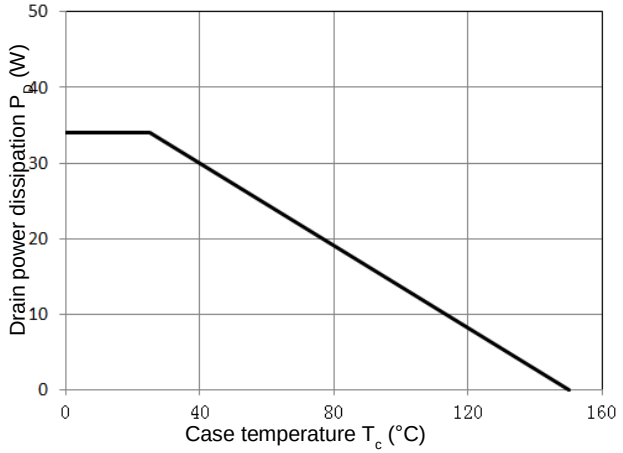


Figure 10.2 Power Dissipation vs. Temperature
TO-247

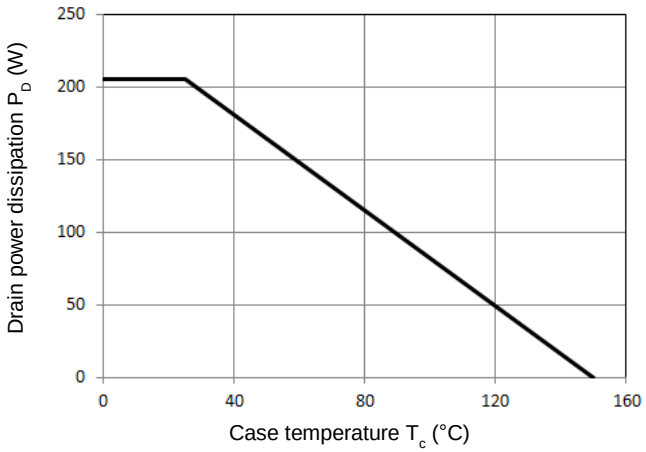


Figure 11.1 Transient Thermal Response Curve

TO-220MF

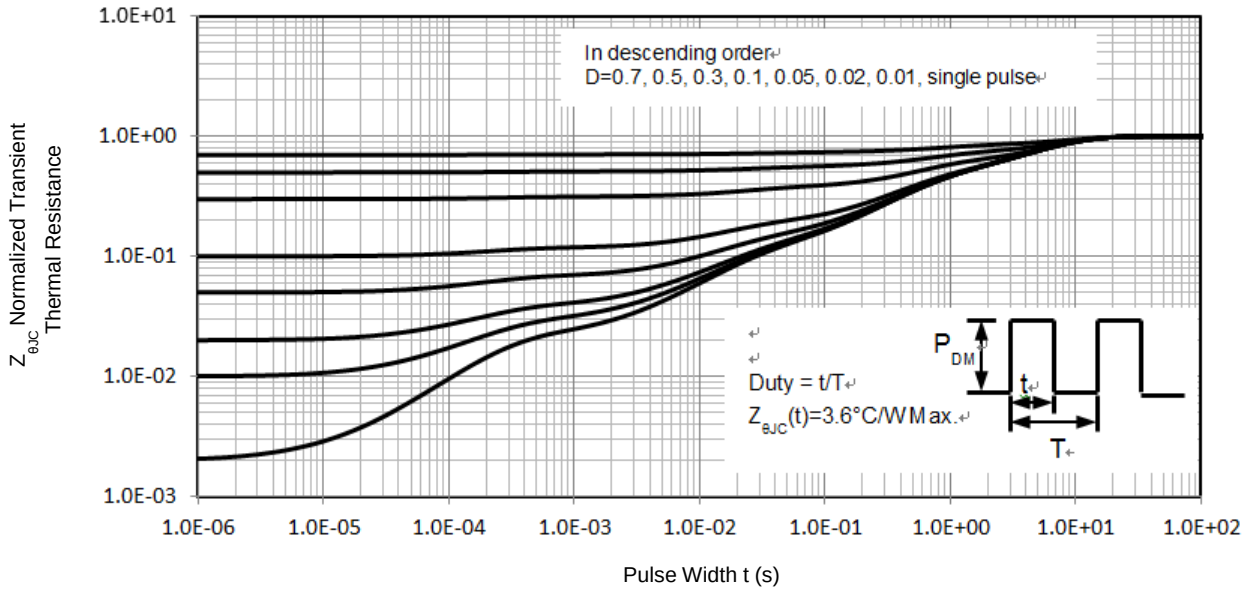
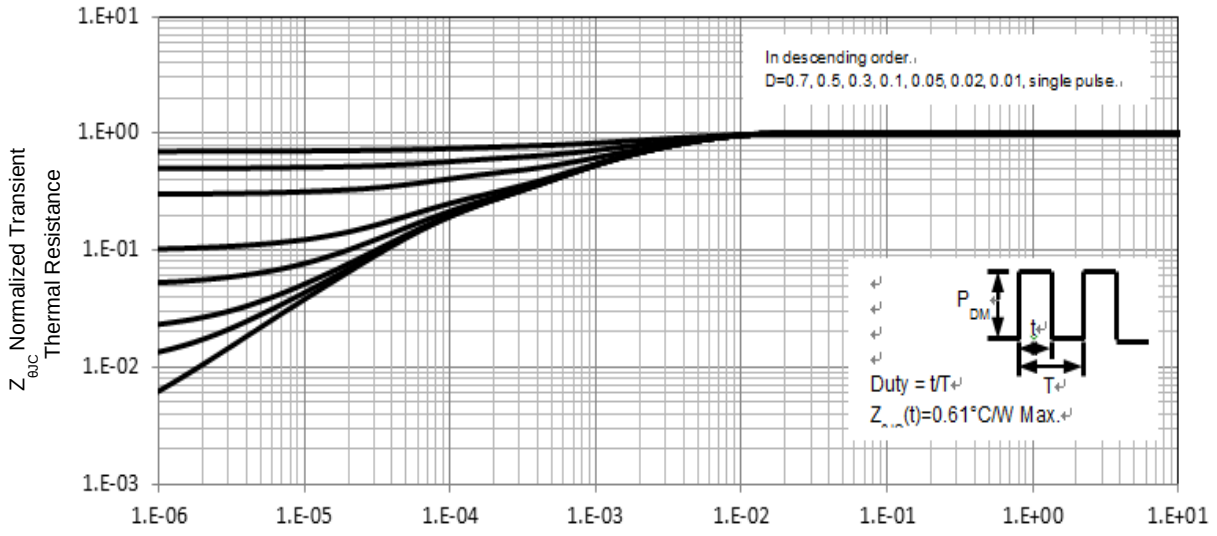
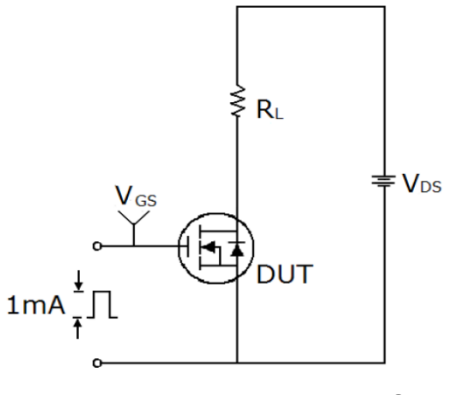


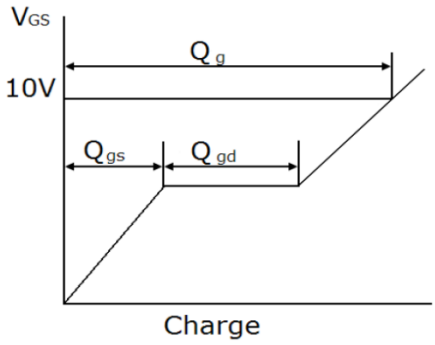
Figure 11.2 Transient Thermal Response Curve

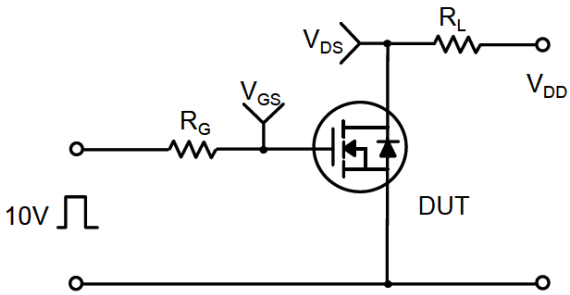
TO-247

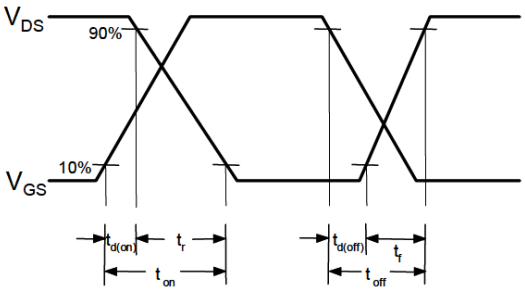


Gate Charge Test Circuit & Waveform

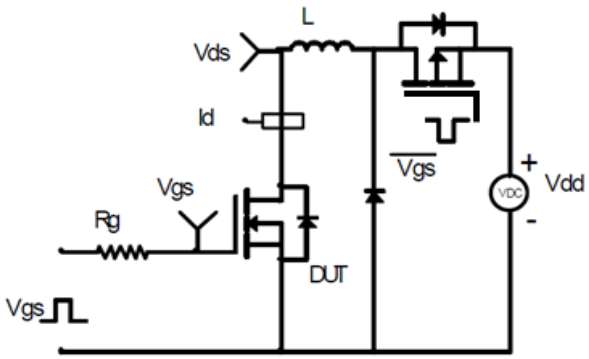


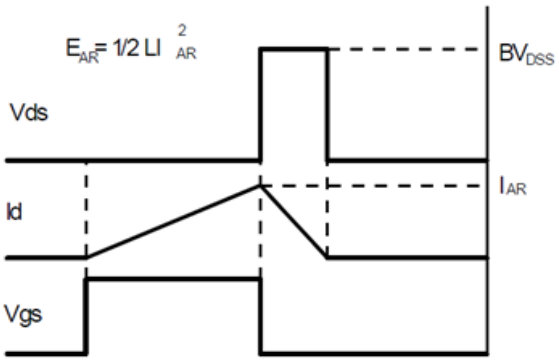




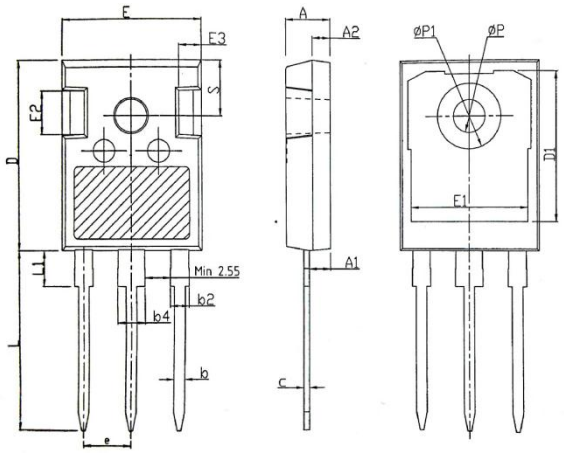


Unclamped Inductive Switching Test Circuit & Waveforms



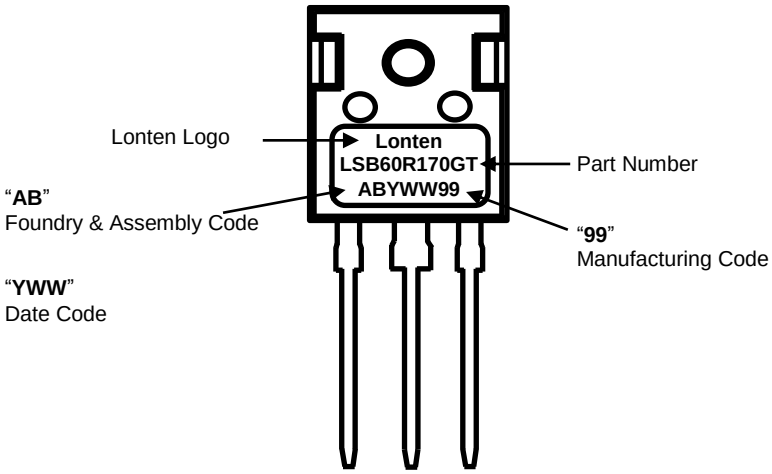


Mechanical Dimensions for TO-247

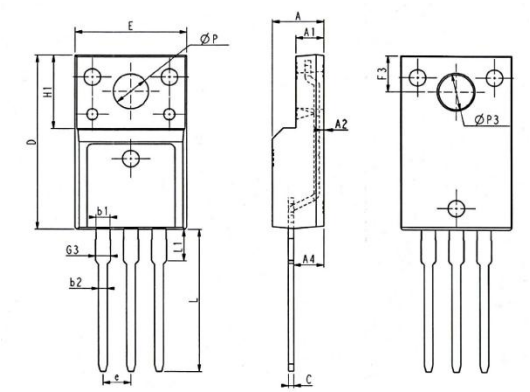


SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e		5.44BSC	
L	19.82	19.92	20.22
L1	—	—	4.30
ØP	3.40	3.60	3.80
ØP1	—	—	7.30
S		6.15BSC	

TO-247 Part Marking Information

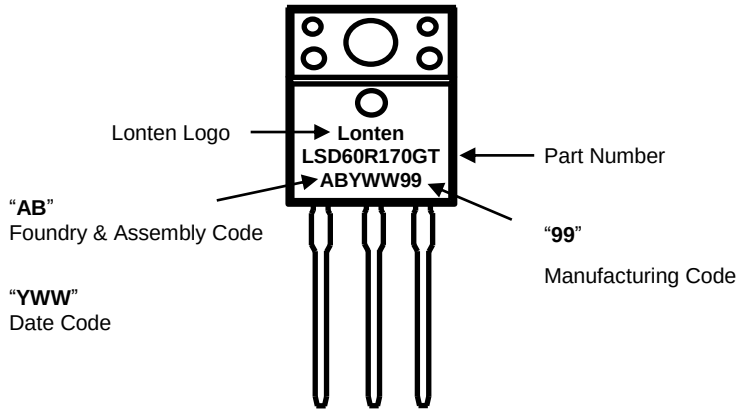


Mechanical Dimensions for TO-220MF



COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408
A	4.50	4.70	4.90	0.177	0.185	0.193
A1	2.34	2.54	2.74	0.092	0.100	0.108
A2	0.30	0.45	0.60	0.012	0.002	0.024
A4	2.65	2.76	2.96	0.104	0.109	0.117
C	0.40	0.50	0.65	0.016	0.020	0.026
D	15.57	15.87	16.17	0.613	0.625	0.637
H1	6.70REF			0.264REF		
e	2.54BSC			0.1BSC		
ØP	3.03	3.18	3.38	0.119	0.125	0.133
L	12.68	12.98	13.28	0.499	0.511	0.523
L1	2.88	3.03	3.18	0.113	0.119	0.125
ØP3	3.15REF			0.124REF		
F3	3.15	3.30	3.45	0.124	0.130	0.136
G3	1.25	1.35	1.55	0.049	0.053	0.061
b1	1.18	1.28	1.43	0.046	0.050	0.056
b2	0.70	0.80	0.95	0.028	0.031	0.037

TO-220MF Part Marking Information



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